

TO-92 Plastic-Encapsulate Transistors

MPSA05 TRANSISTOR (NPN)

FEATURES

- General Purpose Amplifier

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

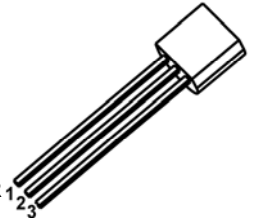
Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	0.5	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

TO – 92

1.EMITTER

2.BASE

3.COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=60\text{V}, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	100			
	$h_{FE(2)}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.25	V
Base-emitter voltage	V_{BE}	$I_C=100\text{mA}, V_{CE}=1.0\text{V}$			1.2	V
Transition frequency	f_T	$V_{CE}=2.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100			MHz